Application No.: TBA 3 Docket No.: 8733.430.10-US

IN THE CLAIMS:

1-23. (Cancelled)

24. (Original) A method of forming a liquid crystal display device, comprising:

forming a gate line on a substrate, the gate line extending along a first direction and having an opening therein;

forming a first insulating layer on the gate line;

forming a semiconductor layer on the first insulating layer over at least a portion of the opening;

forming a data line on the insulating layer extending along a second direction substantially perpendicular to the first direction, a drain electrode on the semiconductor layer over at least a portion of the opening and, and a source electrode on the semiconductor layer extending from the data line and separated and spaced apart from the drain electrode.

- 25. (Original) The method of claim 24, further comprising forming a second insulation layer over the semiconductor layer and the source and drain electrodes, the second insulation layer having a drain contact hole that exposes a portion of the drain electrode.
- 26. (Original) The method of claim 25, further comprising forming a pixel electrode in a pixel region that is defined by an intersection of the gate and data lines, the pixel electrode contacting the drain electrode through the drain contact hole.
- 27. (Original) The method of claim 24, wherein the opening in the gate line is formed in substantially a "T" shape.

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28. (Original) The method of claim 24, wherein the source electrode is formed to substantially surround the drain electrode.

- 29. (Original) The method of claim 24, wherein the drain electrode is formed in substantially a "T" shape.
- 30. (Original) The method of claim 24, wherein forming the drain electrode comprises forming a first portion which overlaps the opening and a second portion which overlaps the gate line on at least two opposing sides of the opening.